

NTHL020N090SC1

Silicon Carbide MOSFET, N-Channel, 900 V, 20 mΩ, TO247-3L

Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- Ultra Low Gate Charge
- High Junction Temperature
- 900V Rating
- 100% UIL Tested
- RoHS Compliant

Benefits



- 196nC
- 175°C

Applications

- UPS
- DC-DC Converter
- Boost Inverter

End Products

- Solar
- Power Devices

Part Electrical Specifications											
Product	Pricing (\$/Unit)	Compliance	Status	Family	Blocking Voltage BV _{DSS} (V)	I _{D(max)} (A)	R _{DS(on) Typ @ 25°C (mΩ)}	Q _{g Total} (nC)	Output Capacitance (pF)	T _{j Max} (°C)	Package Type
NTHL020N090SC1	15.4784	 	Active	M2	900	118	20	196	296	175	TO-247-3LD